

MOSFETs Silicon N-channel MOS (U-MOSVIII-H)

TK72E12N1

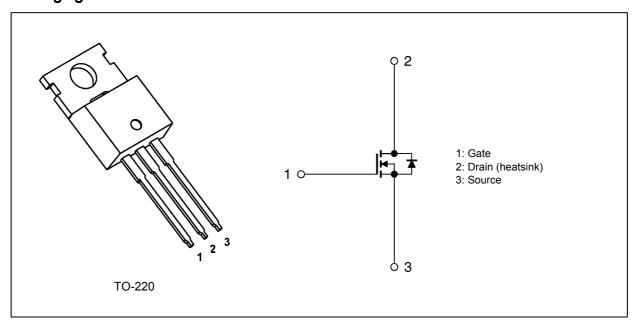
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 3.6 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (2) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 120 \text{ V)}$
- (3) Enhancement mode: V_{th} = 2.0 to 4.0 V (V_{DS} = 10 V, I_{D} = 1.0 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characterist	Symbol	Rating	Unit		
Drain-source voltage			V_{DSS}	120	V
Gate-source voltage			V_{GSS}	±20	
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	I_D	179	Α
Drain current (DC)		(Note 1), (Note 3)	Ι _D	72]
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I _{DP}	360	
Power dissipation	$(T_c = 25^{\circ}C)$		P_{D}	255	W
Single-pulse avalanche energy		(Note 4)	E _{AS}	256	mJ
Avalanche current			I _{AR}	72	Α
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.49	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	83.3	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Limited by silicon chip capability. Package limit is 100 A.

Note 3: Device mounted with heatsink so that $R_{th(ch-a)}$ becomes 2.77°C/W.

Note 4: V_{DD} = 80 V, T_{ch} = 25°C (initial), L = 48.3 $\mu H,\ I_{AR}$ = 72 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$		_	±0.1	μΑ
Drain cut-off current	I _{DSS}	V _{DS} = 120 V, V _{GS} = 0 V	-	-	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	120	_	_	V
Drain-source breakdown voltage (Note 5)	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	90	_	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 1.0 mA	2.0	_	4.0	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 36 A		3.6	4.4	mΩ

Note 5: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition		Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 60 V, V _{GS} = 0 V, f = 1 MHz	_	8100		pF
Reverse transfer capacitance	C _{rss}		_	30	_	
Output capacitance	C _{oss}			1200		
Gate resistance	r _g	_	_	2.4		Ω
Switching time (rise time)	t _r	See Figure 6.2.1	_	33	_	ns
Switching time (turn-on time)	t _{on}		_	64	_	
Switching time (fall time)	t _f		_	37	_	
Switching time (turn-off time)	t _{off}		_	120		

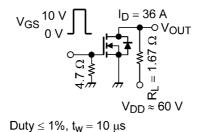


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 96 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 72 \text{ A}$	ı	130	1	nC
Gate-source charge 1	Q _{gs1}		_	44		
Gate-drain charge	Q_{gd}		_	34	_	
Gate switch charge	Q_{SW}		_	52		



6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 6)	I _{DR}	_	_	_	72	Α
Reverse drain current (pulsed)	(Note 6)	I _{DRP}	_	_	_	360	
Diode forward voltage		V _{DSF}	I _{DR} = 72 A, V _{GS} = 0 V	_	_	-1.2	V
Reverse recovery time	(Note 7)	t _{rr}	I _{DR} = 72 A, V _{GS} = 0 V	_	110	_	ns
Reverse recovery charge	(Note 7)	Q _{rr}	-dI _{DR} /dt = 100 A/μs	_	290	_	nC

Note 6: Ensure that the channel temperature does not exceed 150°C.

Note 7: Ensure that V_{DS} peak does not exceed V_{DSS} .

7. Marking

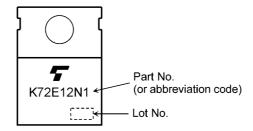


Fig. 7.1 Marking

8. Characteristics Curves (Note)

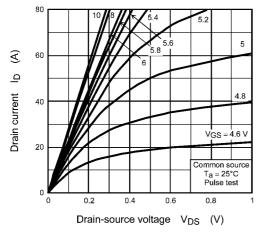
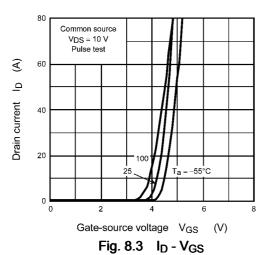


Fig. 8.1 $I_D - V_{DS}$



100

Common source

T_a = 25°C Pulse test

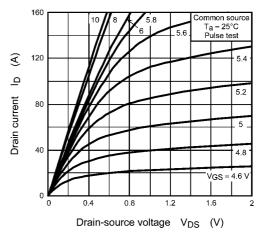


Fig. 8.2 I_D - V_{DS}

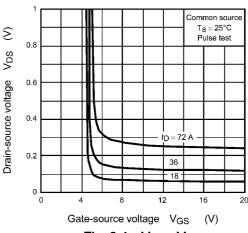


Fig. 8.4 V_{DS} - V_{GS}

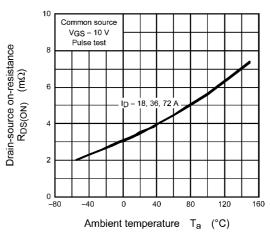


Fig. 8.6 R_{DS(ON)} - T_a

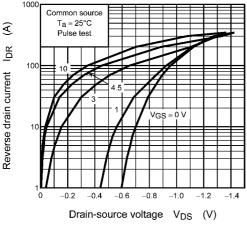


Fig. 8.7 I_{DR} - V_{DS}

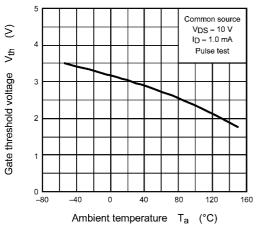


Fig. 8.9 V_{th} - T_a

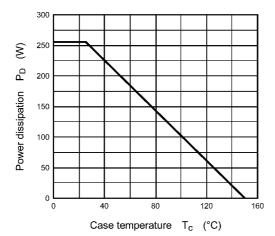


Fig. 8.11 P_D - T_c (Guaranteed Maximum)

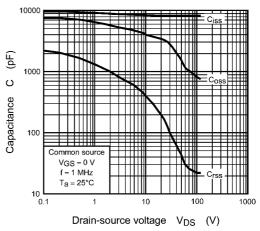


Fig. 8.8 Capacitance - V_{DS}

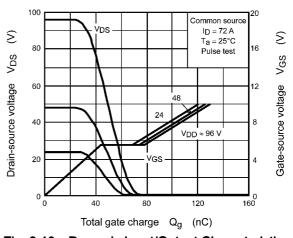


Fig. 8.10 Dynamic Input/Output Characteristics

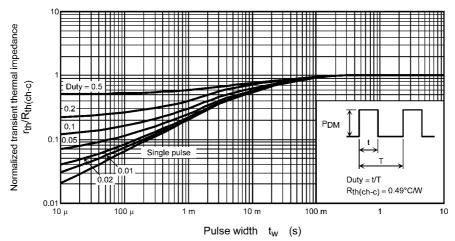


Fig. 8.12 $r_{th}/R_{th(ch-c)} - t_w$ (Guaranteed Maximum)

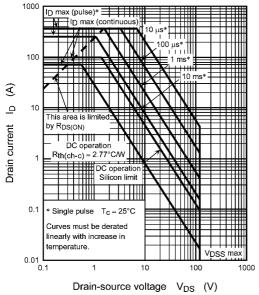


Fig. 8.13 Safe Operating Area (Guaranteed Maximum)

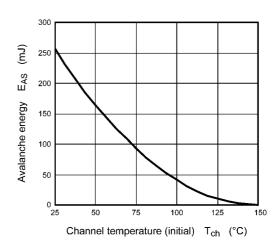


Fig. 8.14 E_{AS} - T_{ch} (Guaranteed Maximum)

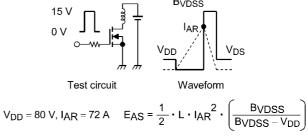


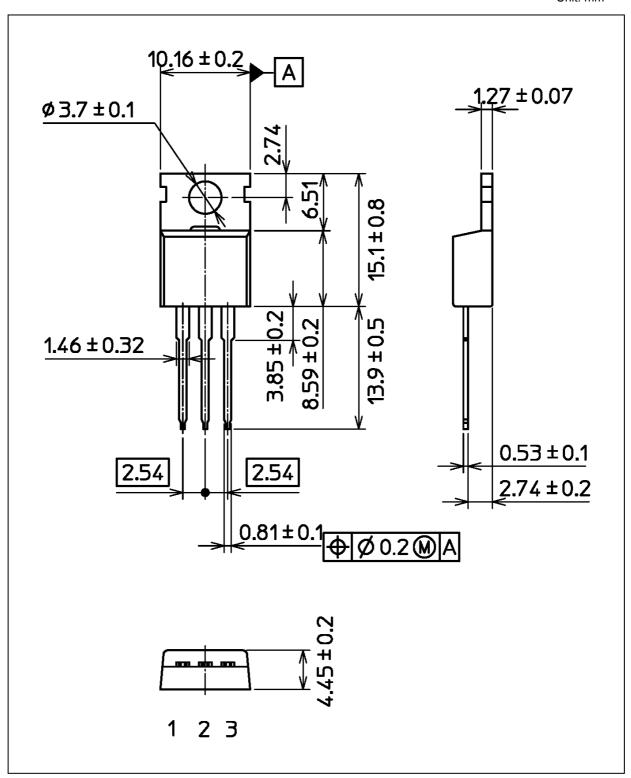
Fig. 8.15 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 1.93 g (typ.)

Package Name(s)
TOSHIBA: 2-10X1A
Nickname: TO-220



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